

second voltage are applied in order between the anode and the cathode, thereby making a portion where a reverse-bias current flows between the anode and the cathode insulating or highly resistive, and the first voltage and the second voltage are reverse bias voltages of different levels.

5 According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device having an EL element that includes an anode, an EL layer, and a cathode, the EL layer being in contact with the anode and the cathode being in contact with the EL layer, characterized in that a voltage applied between the anode and the cathode is gradually changed from a first voltage to a  
10 second voltage, thereby making a portion where a reverse-bias current flows between the anode and the cathode insulating or highly resistive, and the first voltage and the second voltage are reverse bias voltages of different levels.

According to the present invention, a method of fabricating and/or repairing a light emitting device can be characterized in that the first voltage and the second  
15 voltage are within  $\pm 15\%$  of an avalanche voltage of the EL element.

According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device by applying a first voltage and a second voltage to an EL element in order, characterized in that the first voltage is a ground voltage while the second voltage is a reverse bias voltage.

20 According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device by gradually changing a voltage applied to an EL element from a first voltage to a second voltage, characterized in that one of the first voltage and the second voltage is a ground voltage while the other is a reverse bias voltage.

25 According to the present invention, there is provided a method of fabricating

and/or repairing a light emitting device having an EL element that includes an anode, an EL layer, and a cathode, the EL layer being in contact with the anode and the cathode being in contact with the EL layer, characterized in that a first voltage and a second voltage are applied in order between the anode and the cathode, and the first  
5 voltage is a ground voltage while the second voltage is a reverse bias voltage.

According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device having an EL element that includes an anode, an EL layer, and a cathode, the EL layer being in contact with the anode and the cathode being in contact with the EL layer, characterized in that a voltage applied  
10 between the anode and the cathode is gradually changed from a first voltage to a second voltage, and one of the first voltage and the second voltage is a ground voltage while the other is a reverse bias voltage.

According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device having an EL element that includes an anode, an EL layer, and a cathode, the EL layer being in contact with the anode and the cathode being in contact with the EL layer, characterized in that a first voltage and a second voltage are applied in order between the anode and the cathode, thereby making a portion where a reverse-bias current flows between the anode and the cathode insulating or highly resistive, and the first voltage is a ground voltage while  
15 the second voltage is a reverse bias voltage.

According to the present invention, there is provided a method of fabricating and/or repairing a light emitting device having an EL element that includes an anode, an EL layer, and a cathode, the EL layer being in contact with the anode and the cathode being in contact with the EL layer, characterized in that a voltage applied  
25 between the anode and the cathode is gradually changed from a first voltage to a

second voltage, thereby making a portion where a reverse-bias current flows between the anode and the cathode insulating or highly resistive, and one of the first voltage and the second voltage is a ground voltage while the other is a reverse bias voltage.

According to the present invention, a method of fabricating and/or repairing a light emitting device can be characterized in that the reverse bias voltage is within  $\pm 15\%$  of an avalanche voltage of the EL element.

### BRIEF DESCRIPTION OF THE DRAWINGS

In the accompanying drawings:

Figs. 1A and 1B are diagrams schematically showing the current flow in an EL element when a reverse bias voltage is applied to the EL element;

Figs. 2A and 2B are diagrams schematically showing a change in voltage-current characteristic of an EL element in the middle of repairing process and the current flow in the EL element when a forward bias voltage is applied to the EL element after repairing;

Fig. 3 is a circuit diagram of a pixel;

Figs. 4A and 4B are circuit diagrams of a pixel portion and a diagram showing the operation of the pixel portion during repairing, respectively;

Fig. 5 is a circuit diagram of a pixel;

Figs. 6A and 6B are circuit diagrams of a pixel portion and a diagram showing the operation of the pixel portion during repairing, respectively;

Figs. 7A and 7B are diagrams showing the structure of driving circuits;

Figs. 8A and 8B are diagrams showing the structure of driving circuits;

Figs. 9A and 9B are diagrams showing the structure of EL elements;

Figs. 10A and 10B are diagrams showing the structure of EL elements;